TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

HIGH POWERT

P1dB=36.0dBm at 5.9GHz to 6.75GHz

HIGH GAIN

G1dB=8.0dB at 5.9GHz to 6.75GHz

MICROWAVE POWER GaAs FET TIM5964-4SL-251 PRELIMINARY

- BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS $(Ta = 25^{\circ}C)$

| CHARACTERISTICS | SYMBOL | CONDITION | UNIT | MIN. | TYP. | MAX. |
|---------------------------------------|--------------|----------------------|------|------|------|------|
| Output Power at 1dB | P1dB | | dBm | 35.5 | 36.5 | |
| Compression Point | | | | | | |
| Power Gain at 1dB | G1dB | VDS= 10V | dB | 8.0 | | |
| Compression Point | | f= 5.9 to 6.75GHz | | | | |
| Drain Current | IDS1 | | А | | 1.1 | 1.3 |
| Gain Flatness | ΔG | | dB | | | ±0.6 |
| Power Added Efficiency | η_{add} | | % | | 32 | |
| 3 rd Order Intermodulation | IM3 | | dBc | -42 | -45 | |
| Distortion | | NOTE | | | | |
| Drain Current | IDS2 | | Α | | 1.1 | 1.3 |
| Channel Temperature Rise | ΔTch | VDS X IDS X Rth(c-c) | °C | | | 80 |

NOTE : Two Tone Test, Po=25.5dBm (Single Carrier Level)

ELECTRICAL CHARACTERISTICS $(Ta = 25^{\circ}C)$

| CHARACTERISTICS | SYMBOL | CONDITION | UNIT | MIN. | TYP. | MAX. |
|-------------------------|----------|-----------------|------|------|------|------|
| Transconductance | gm | VDS= 3V | mS | _ | 900 | _ |
| | | IDS= 1.5A | | | | |
| Pinch-off Voltage | VGSoff | VDS= 3V | V | -1.0 | -2.5 | -4.0 |
| | | IDS= 15mA | | | | |
| Saturated Drain Current | IDSS | VDS= 3V | Α | _ | 2.6 | 3.5 |
| | | VGS= 0V | | | | |
| Gate-Source Breakdown | VGSO | IGS= -50μΑ | V | -5 | | |
| Voltage | | | | | | |
| Thermal Resistance | Rth(c-c) | Channel to Case | °C/W | | 4.5 | 6.5 |

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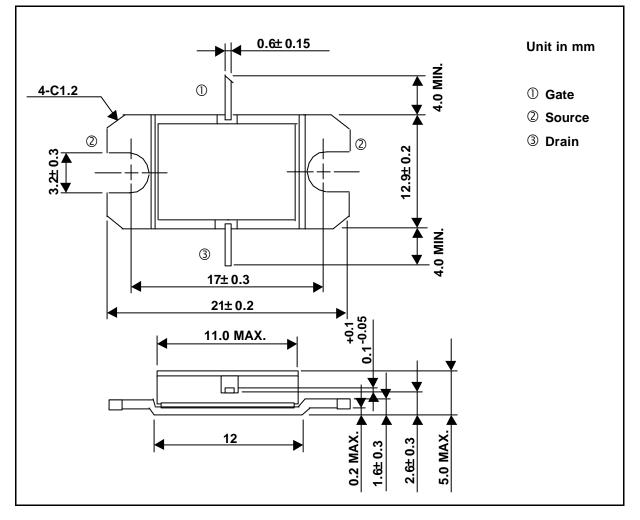
The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

TIM5964-4SL-251

ABSOLUTE MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

| CHARACTERISTICS | SYMBOL | UNIT | RATING |
|-------------------------------------|--------|------|-------------|
| Drain-Source Voltage | VDS | V | 15 |
| Gate-Source Voltage | VGS | V | -5 |
| Drain Current | IDS | А | 3.5 |
| Total Power Dissipation (Tc= 25 °C) | РТ | W | 23.0 |
| Channel Temperature | Tch | °C | 175 |
| Storage Temperature | Tstg | °C | -65 to +175 |

PACKAGE OUTLINE (2-11D1B)



HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.